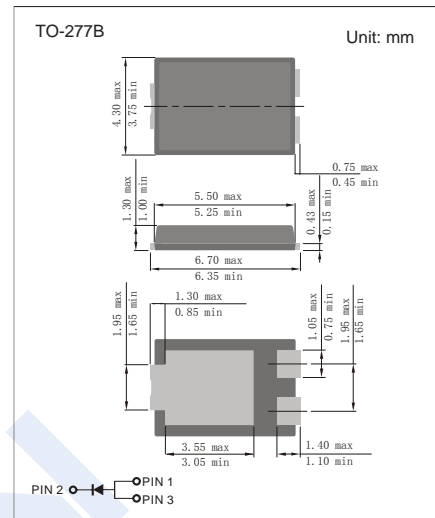


## Schottky Diodes

### KBR15T50DF5

#### ■ Features

- Low Forward Voltage Drop
- Excellent High Temperature Stability
- Trench Schottky Design using 8" Advanced Technology
- Lead Free Finish, RoHS Compliant
- Excellent ESD protection



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	VRRM	50	V
Working Peak Reverse Voltage	VRWM	50	
DC Blocking Voltage	VR	50	
Average Forward Rectified Current	IFAV	15	A
Peak Forward Surge Current @ 60Hz	IFSM	300	
Thermal Resistance Junction to Case	$R_{\theta JC}$	13	$^\circ\text{C}/\text{W}$
Junction Temperature	TJ	150	$^\circ\text{C}$
Storage Temperature range	Tstg	-65 to 150	

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	VR	IR= 0.5 mA	50			V
Forward voltage	VF1	IF= 3 A, TJ=25 $^\circ\text{C}$			0.5	
	VF2	IF= 3 A, TJ=125 $^\circ\text{C}$		0.28		
	VF3	IF= 15 A, TJ=25 $^\circ\text{C}$			0.54	
	VF4	IF= 15 A, TJ=125 $^\circ\text{C}$		0.44		
Reverse voltage leakage current	IR1	VR= 50 V, TJ=25 $^\circ\text{C}$			50	$\mu\text{A}$
	IR2	VR= 50 V, TJ=125 $^\circ\text{C}$		12		mA

## Schottky Diodes

## KBR15T50DF5

■ Typical Characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Fig.1 Forward Current Derating Curve

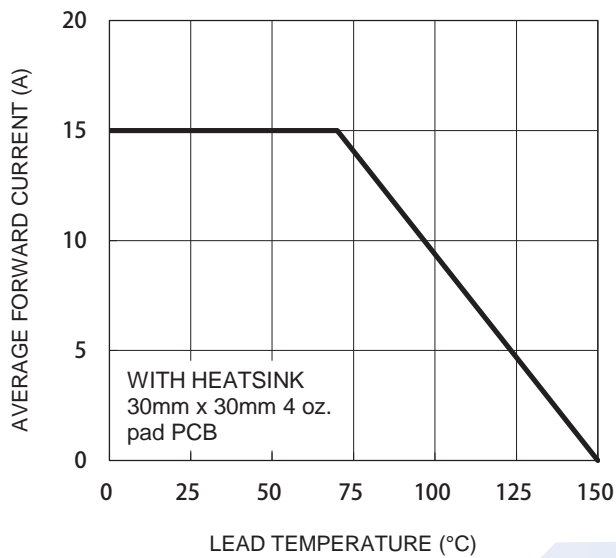


Fig.2 Typical Junction Capacitance

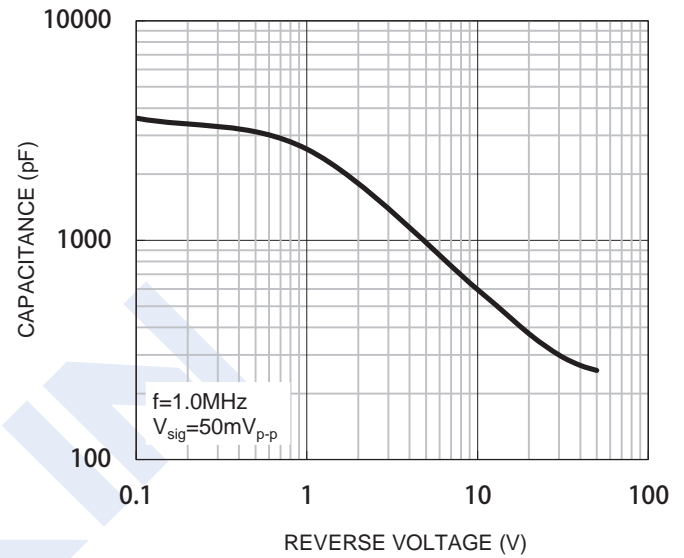


Fig.3 Typical Reverse Characteristics

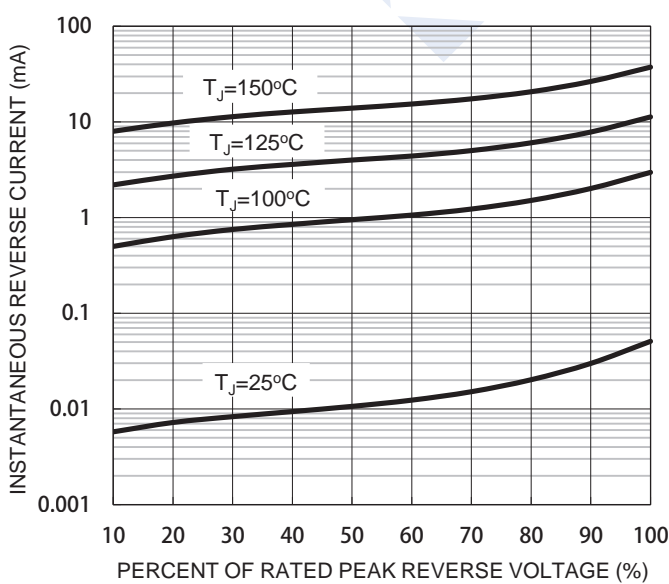


Fig.4 Typical Forward Characteristics

